

Description

The SX01P101 uses advanced trench technology to provide excellent RDS(ON) , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

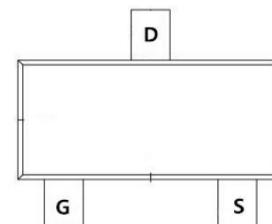
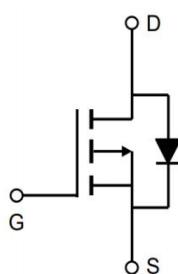
General Features

$V_{DS} = -100V$ $I_D = -0.9 A$

$R_{DS(ON)} < 0.65\Omega$ @ $V_{GS}=-10V$

Application

Battery
protection Load
switch
Uninterruptible power supply



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-0.9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-0.7	A
I_{DM}	Pulsed Drain Current ²	-1.8	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	80	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-100	---	---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.0624	---	$\text{V}/^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=-10\text{V}$, $I_D=-0.8\text{A}$	---	0.52	0.65	Ω
		$V_{GS}=-4.5\text{V}$, $I_D=-0.4\text{A}$	---	0.56	0.7	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu\text{A}$	-1.0	-1.5	-2.5	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	4.5	---	$\text{mV}/^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-80\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	-10	uA
		$V_{DS}=-80\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	-100	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-0.8\text{A}$	---	3	---	S
R _g	Gate Resistance	$V_{DS}=0\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	16	32	Ω
Q _g	Total Gate Charge (-4.5V)	$V_{DS}=-15\text{V}$, $V_{GS}=-4.5\text{V}$, $I_D=-0.5\text{A}$	---	4.5	---	nC
Qgs	Gate-Source Charge		---	1.14	---	
Qgd	Gate-Drain Charge		---	1.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-50\text{V}$, $V_{GS}=-10\text{V}$, $R_G=3.3\Omega$ $I_D=-0.5\text{A}$	---	13.6	---	ns
Tr	Rise Time		---	6.8	---	
Td(off)	Turn-Off Delay Time		---	34	---	
T _f	Fall Time		---	3	---	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	553	---	pF
Coss	Output Capacitance		---	29	---	
Crss	Reverse Transfer Capacitance		---	20	---	
IS	Continuous Source Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	-0.9	A
ISM	Pulsed Source Current ^{2,4}		---	---	-1.8	A
VSD	Diode Forward Voltage ²	$V_{GS}=0\text{V}$, $I_S=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150°C junction temperature4 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

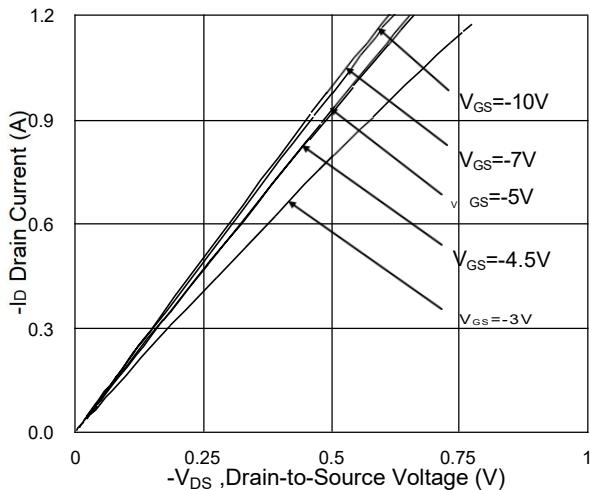


Fig.1 Typical Output Characteristics

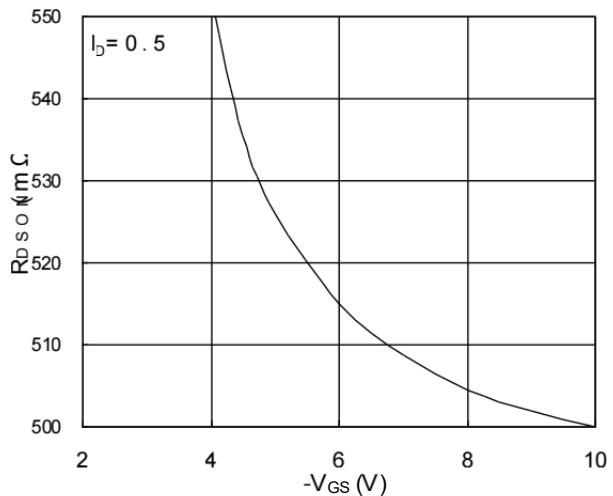


Fig.2 On-Resistance vs. Gate-Source

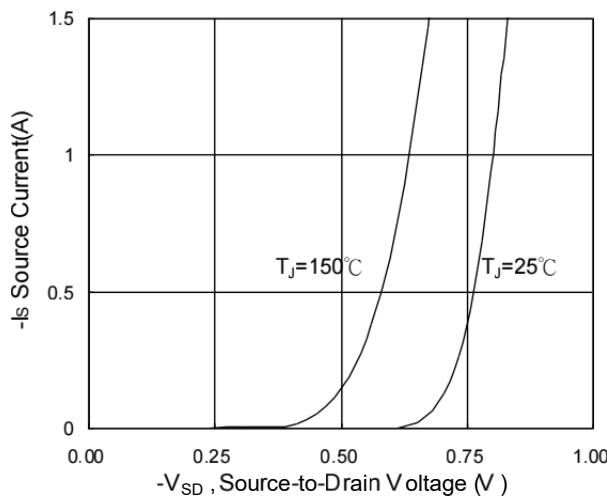


Fig.3 Forward Characteristics Of Reverse

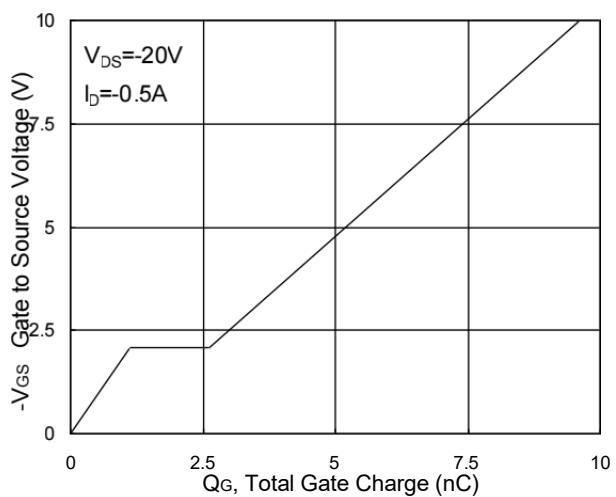


Fig.4 Gate-Charge Characteristics

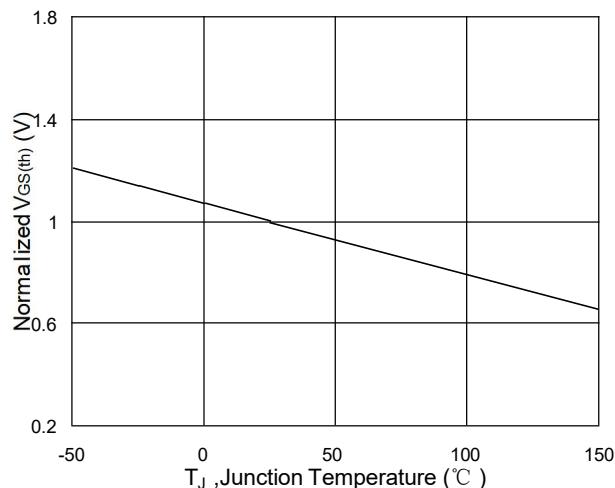


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

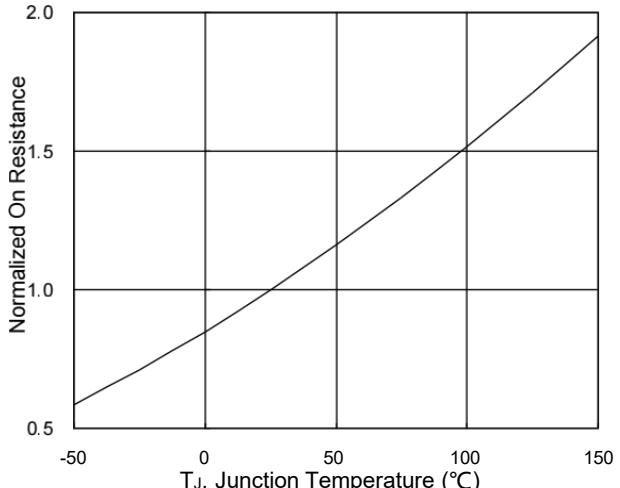


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

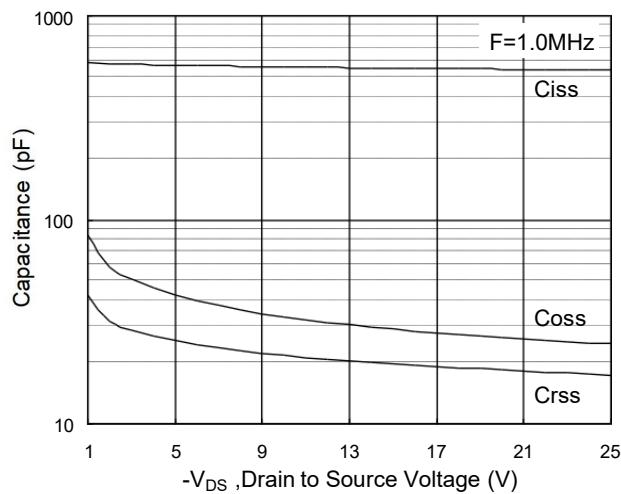


Fig.7 Capacitance

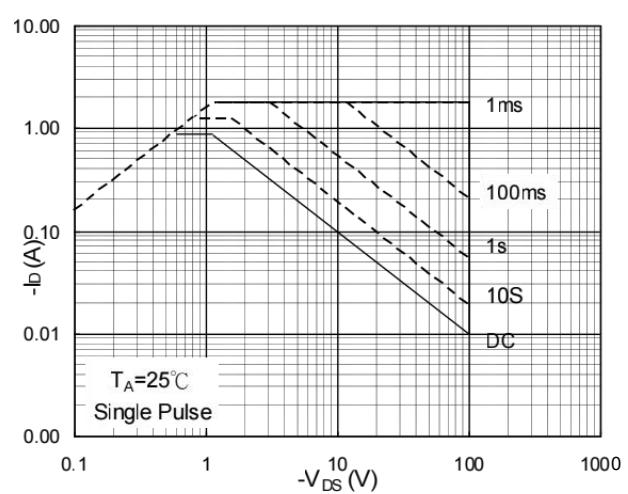


Fig.8 Safe Operating Area

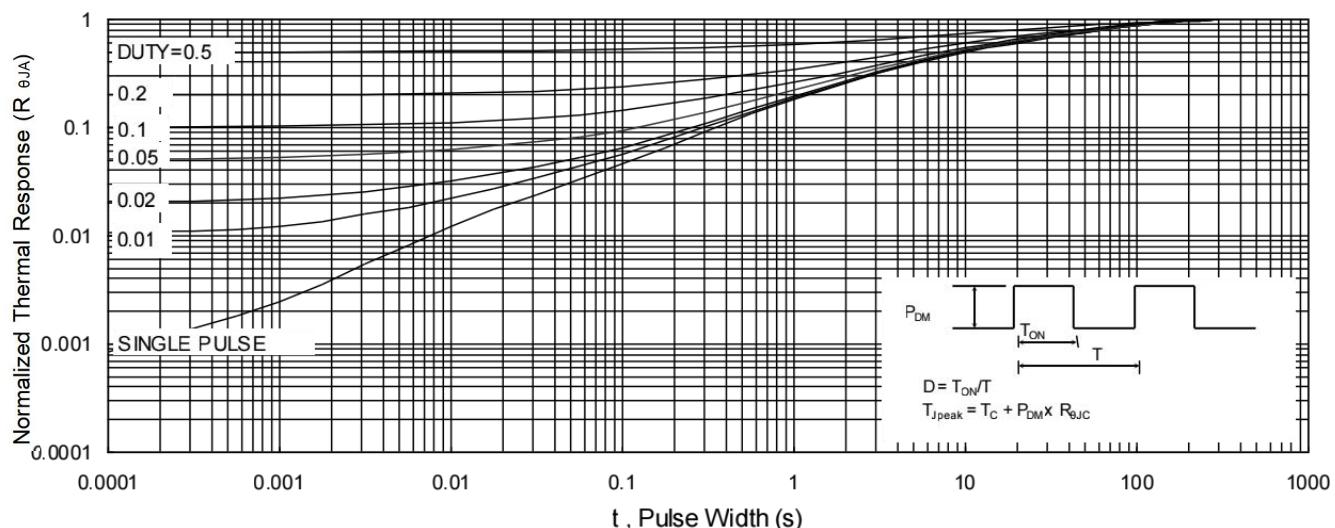


Fig.9 Normalized Maximum Transient Thermal Impedance

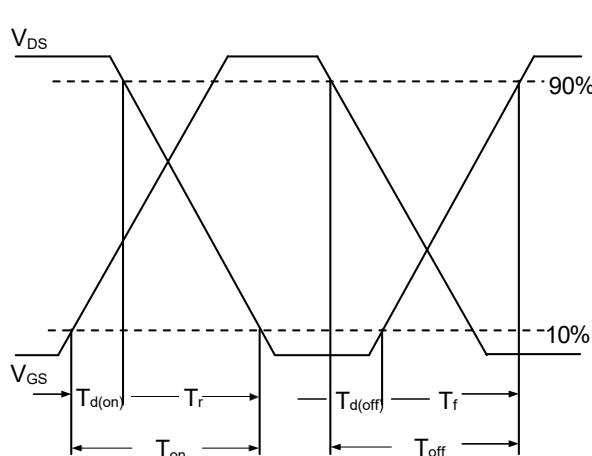


Fig.10 Switching Time Waveform

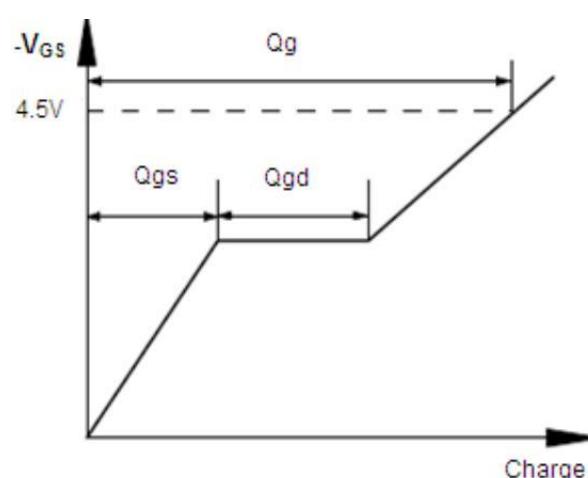
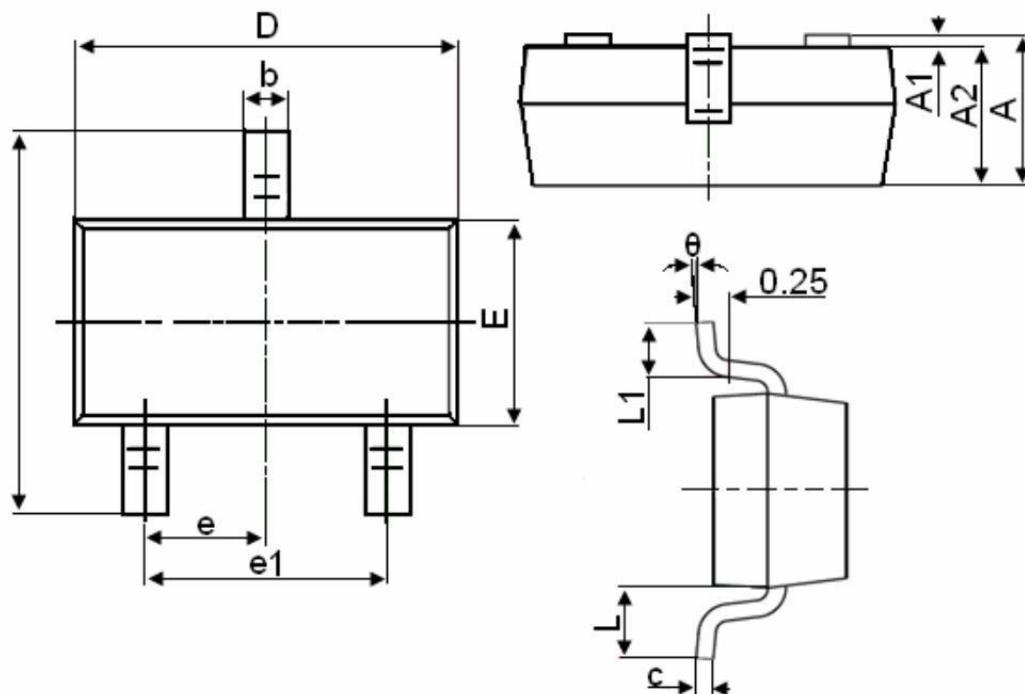


Fig.11 Gate Charge Waveform

SOT-23 Package Information

Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT-23		3000